

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 292870-280PCT	SERIAL NO. 10/584,052			
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Stephane POCAS, et al.					
		FILING DATE June 22, 2006	GROUP 2892				
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
/E.J./	AA	6 274 892	08-14-01	KUB, Francis J. et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
/E.J./	AL	38 29 906	03-15-90	DE (with English abstract)	YES	NO	
/E.J./	AM	43 04 349	08-18-94	DE			NO
	AN						
	AO						
	AP						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
/E.J./	AQ	ZHU, Shiyang et al., "Buried Cobalt Silicide Layer Under Thin Silicon Film Fabricated by Wafer Bonding and Hydrogen-Induced Delamination Techniques", Journal of the Electrochemical Society, Vol. 146. NO. 7, pgs. 2712-2716, 1999.					
	AR	HAISMA, Jan, "Contact Bonding, Including Direct-Bonding in a Historical and Recent Context of Materials Science and Technology, Physics and Chemistry Historical Review in a Broader Scope and Comparative Outlook", Materials Science and Engineering, Vol. 37, pgs. 1-58, 2002.					
	AS	XIAO, Zhi-Xiong et al., "Low Temperature Silicon Wafer-to-Wafer Bonding with Nickel Silicide", J. Electrochem. Soc., Vol. 145, No. 4, pgs. 1360-1362, 1998.					
	AT	MORICEAU, H. et al., "The Bonding Energy Control: an Original Way to Debondable Substrates", Electrochemical Society Conf., Vol. 19, 2003.					
	AU	NICOLET, Marc-A et al., "Silicides", VLSI Handbook, pgs. 415-432, 1985.					
	AV	TONG-GOESELE, "Semiconductor Wafer Bonding", The Electrochemical Society Series, pgs. VII-XVIII, 1-15, 49-135, 1998.					
	AW	IYER, S.S. et al., "Silicon Wafer Bonding Technology for VLSI and MEMS Applications", INSPEC, pgs. V-XXV, 1-51, 123-143, 2002.					
	AX	SAKAGUCHI, K. et al., "Eltran By Splitting Porous Si Layers", Electrochemical Society Proceedings, Vol. 99-3, pgs. 116-121, 1999.					
↓	AY	AUBERTON-HERVE, A.J., "Why Can Smart Cut Change the Future of Microelectronics?", International Journal of High Speed Electronics and Systems, Vol. 10, No. 1, pgs.131-146, 2000.					
	AZ				<input type="checkbox"/> Additional References sheet(s) attached		
Examiner /Eric Jones/				Date Considered 1/6/2009			
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							